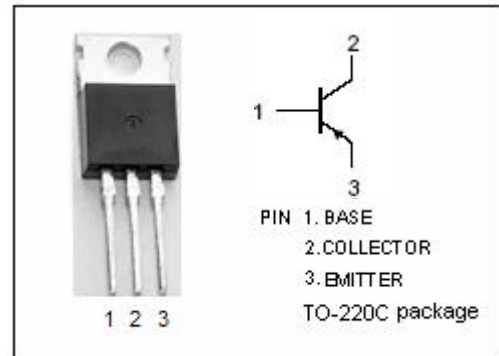


**isc Silicon PNP Power Transistor**
**2SA1012**
**DESCRIPTION**

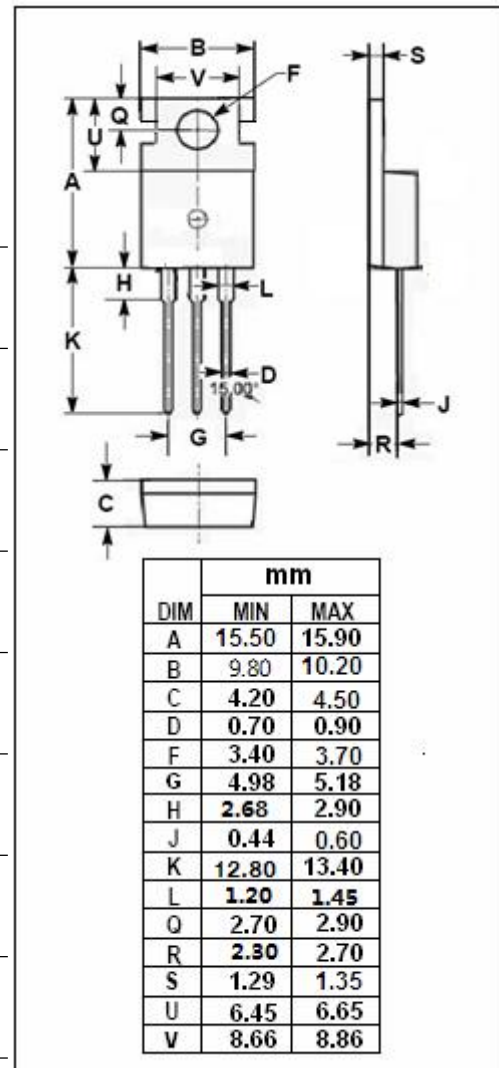
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.4(V)(Max) @ I_C = -3A$
- High Switching Speed
- Complement to Type 2SC2562
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**APPLICATIONS**

- Designed for high current switching applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$P_C$	Total Power Dissipation @ $T_C = 25^\circ C$	25	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon PNP Power Transistor****2SA1012****ELECTRICAL CHARACTERISTICS**T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA ; I <sub>B</sub> = 0	-50			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -50V ; I <sub>E</sub> = 0			-1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -1V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A ; V <sub>CE</sub> = -1V	30			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -4V		60		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1MHz		170		pF

## Switching Times

t <sub>on</sub>	Turn-on Time			0.1		μ s
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = -3A, R <sub>L</sub> = 10 Ω, I <sub>B1</sub> = -I <sub>B2</sub> = -0.15A, V <sub>CC</sub> = -30V		1.0		μ s
t <sub>f</sub>	Fall Time			0.1		μ s

◆ **h<sub>FE-1</sub> Classifications**

O	Y
70-140	120-240

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